

TM70P02D

P-Channel Enhancement Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

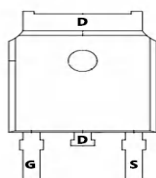
General Features

$V_{DS} = -20V$ $I_D = -70A$
 $R_{DS(ON)} = 4.5m\Omega$ (typ.) @ $V_{GS} = -4.5V$

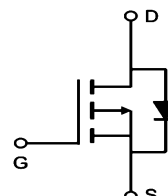
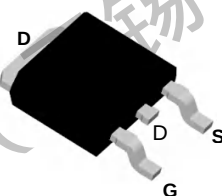
100% UIS Tested
100% R_g Tested



D:TO-252-3L



Marking: 70P02



Absolute Maximum Ratings ($T_C = 25^\circ C$ Unless Otherwise Noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-70	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-42	A
I_{DM}	Pulsed Drain Current ²	-175	A
EAS	Single Pulse Avalanche Energy ³	80	mJ
$P_D @ T_C = 25^\circ C$	Total Power Dissipation ³	43.1	W
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	6.6	$^\circ C/W$



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Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise noted)

Parameter		Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics							
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-20	-	-	V
Gate-body Leakage current		I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 12V$	-	-	± 100	nA
Zero Gate Voltage Drain Current	$T_J=25^{\circ}C$	I_{DSS}	$V_{DS} = -20V, V_{GS} = 0V$	-	-	-1	μA
	$T_J=100^{\circ}C$			-	-	-100	
Gate-Threshold Voltage		$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.4	-0.65	-1.0	V
Drain-Source On-Resistance ⁴		$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -10A$	-	4.5	5.4	mΩ
			$V_{GS} = -2.5V, I_D = -10A$	-	6.4	7.9	
Forward Transconductance ⁴		g_{fs}	$V_{DS} = -4.5V, I_D = -10A$	-	56	-	S
Dynamic Characteristics ⁵							
Input Capacitance		C_{iss}	$V_{DS} = -10V, V_{GS} = 0V, f = 1MHz$	-	4770	-	pF
Output Capacitance		C_{oss}		-	665	-	
Reverse Transfer Capacitance		C_{rss}		-	570	-	
Gate Resistance		R_g	$f = 1MHz$	-	9.6	-	Ω
Switching Characteristics ⁵							
Total Gate Charge		Q_g	$V_{GS} = -4.5V, V_{DS} = -10V, I_D = -10A$	-	55	-	nC
Gate-Source Charge		Q_{gs}		-	5.2	-	
Gate-Drain Charge		Q_{gd}		-	10	-	
Turn-On Delay Time		$t_{d(on)}$	$V_{GS} = -4.5V, V_{DD} = -10V, R_g = 3\Omega, I_D = -10A$	-	22	-	ns
Rise Time		t_r		-	38	-	
Turn-Off Delay Time		$t_{d(off)}$		-	110	-	
Fall Time		t_f		-	62	-	
Drain-Source Body Diode Characteristics							
Diode Forward Voltage ⁴		V_{SD}	$I_S = -10A, V_{GS} = 0V$	-	-	-1.2	V
Continuous Source Current	$T_C=25^{\circ}C$	I_S	-	-	-	-70	A

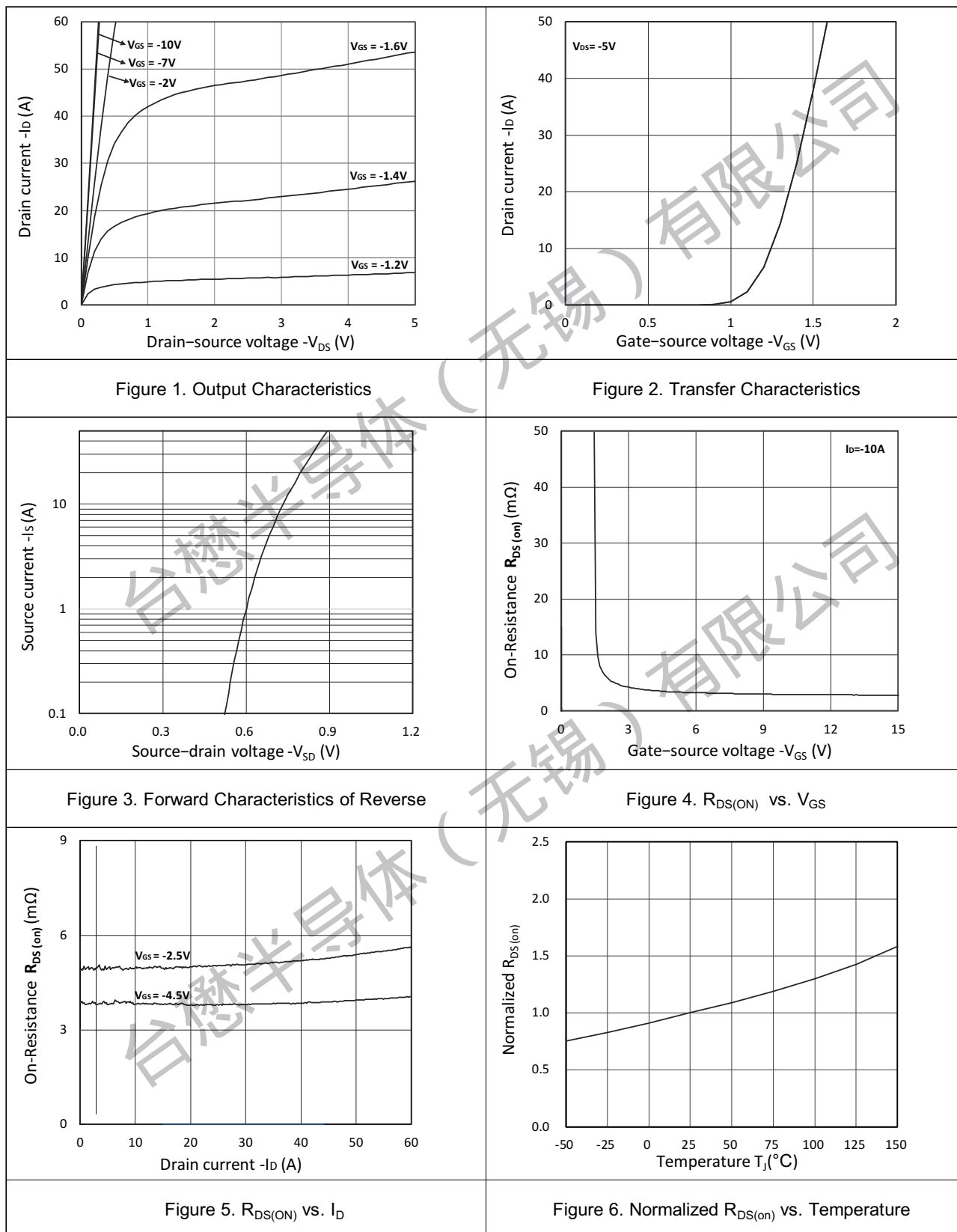
Note :

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)} = 150^\circ\text{C}$.
2. The EAS data shows Max. rating. The test condition is $V_{DD} = -25V, V_{GS} = -10V, L = 0.4\text{mH}, I_{AS} = -20A$.
3. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
5. This value is guaranteed by design hence it is not included in the production test.

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Typical Characteristics



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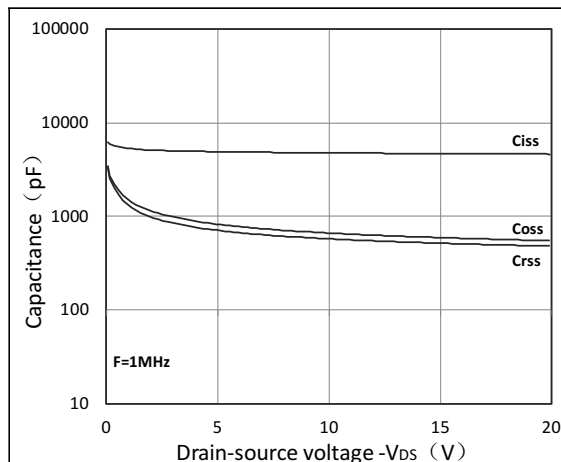


Figure 7. Capacitance Characteristics

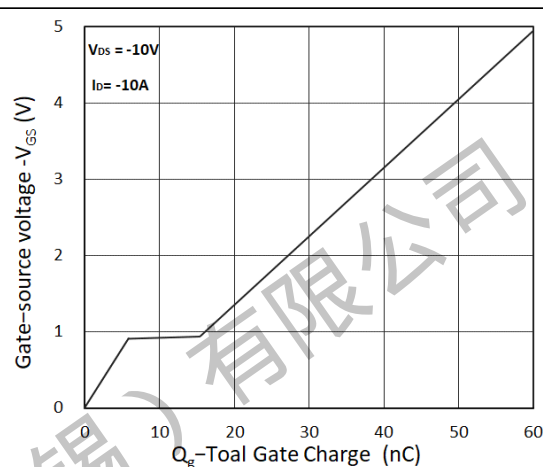


Figure 8. Gate Charge Characteristics

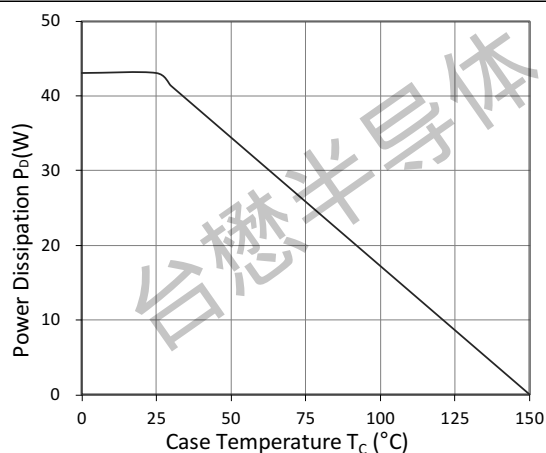


Figure 9. Power Dissipation

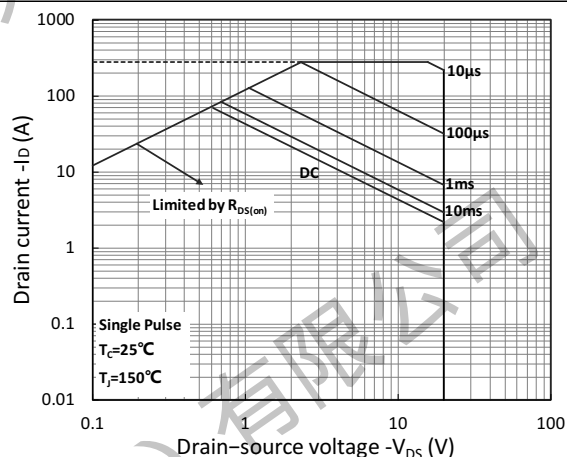


Figure10. Safe Operating Area

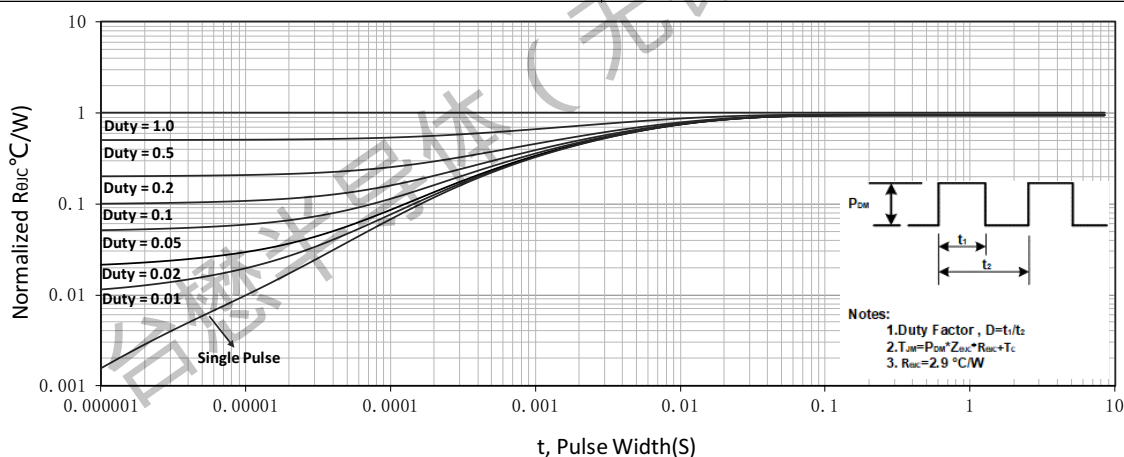
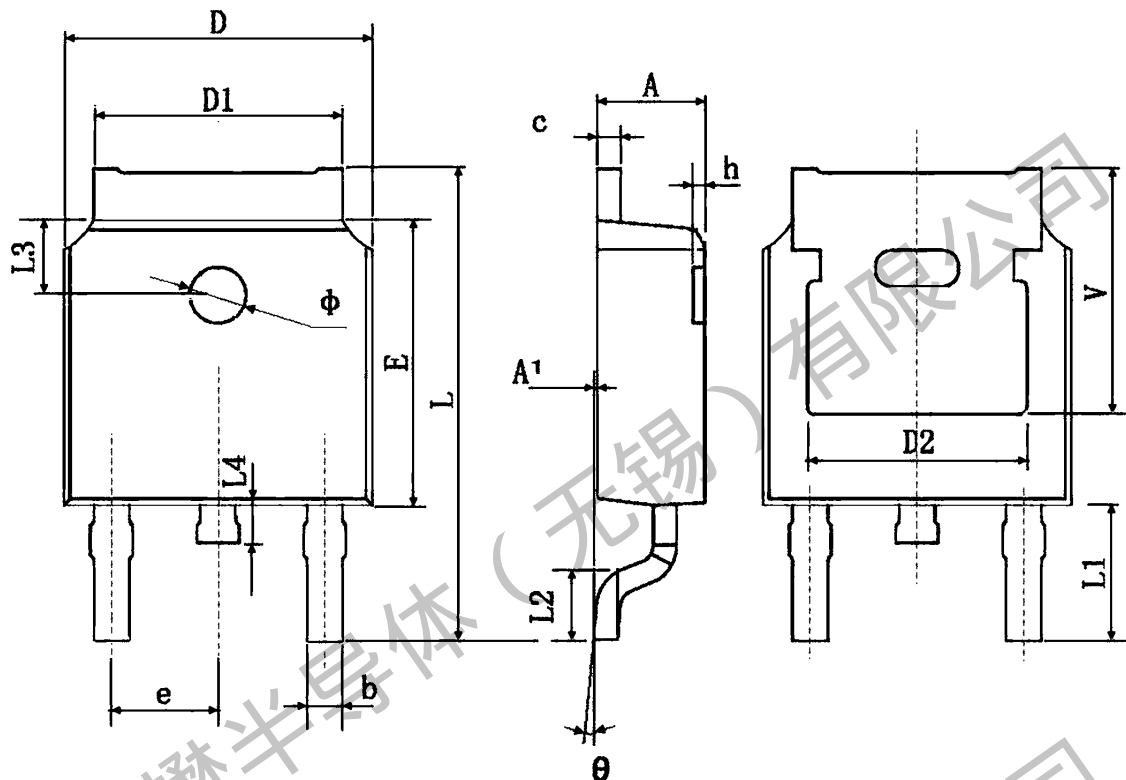


Figure 11. Normalized Maximum Transient Thermal Impedance

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Package Mechanical Data: TO-252-3L



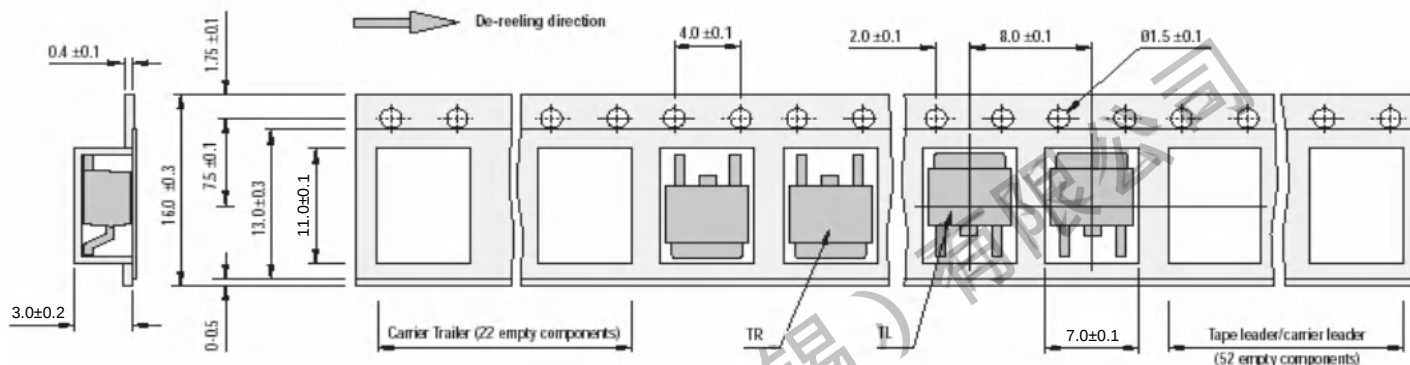
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	



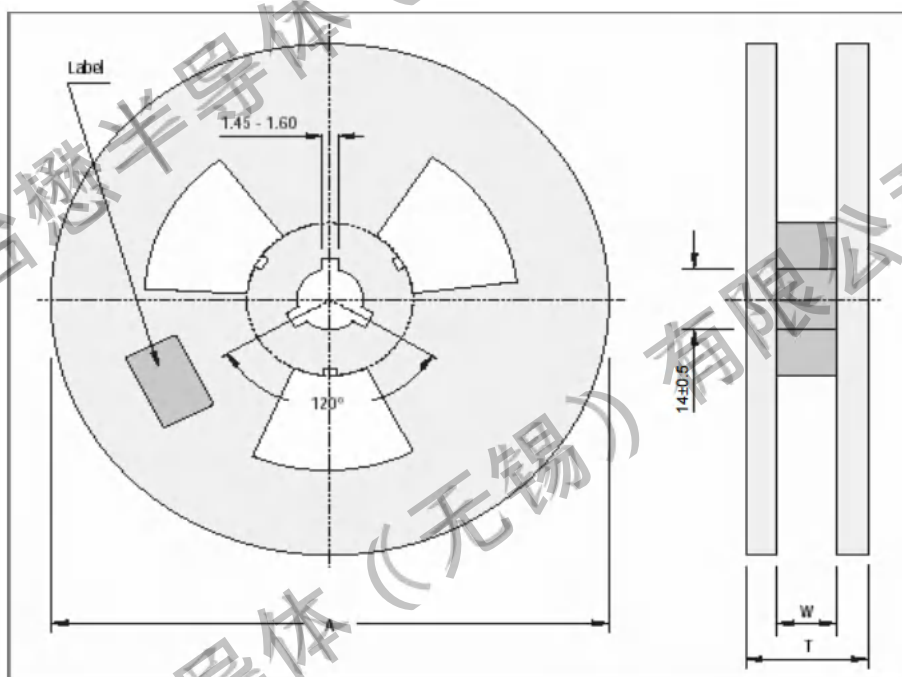
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TO-252-3L Embossed Carrier Tape



TO-252-3L Reel



All Dimensions are in mm.

Reel Specifications				
Package	Tape Width	Reel Dia. A - Max	Inside Thickness W	Reel Thickness T - max
TO-252-3L	16	330	18.0 ± 1.5	20

Packaging Information

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
2,500 pcs	13 inch	5,000 pcs	355×370×50	25,000 pcs	380×275×380	

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Revision history:

Date	Rev	Description	Page
2023.07.01	23.07	Original	